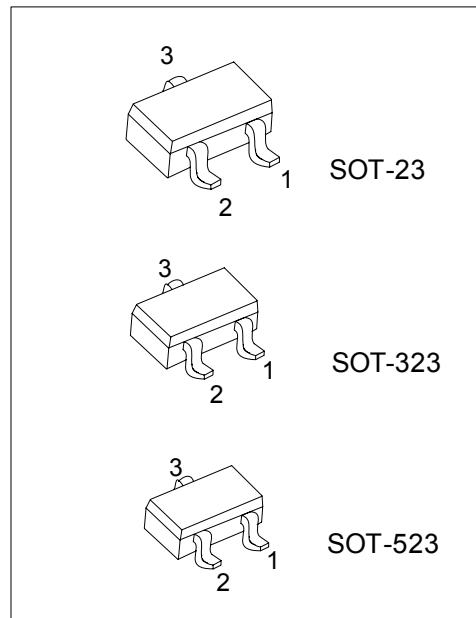
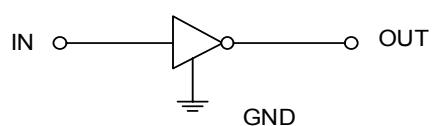
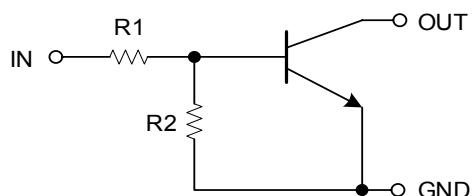


**DTC123E****NPN EPITAXIAL SILICON TRANSISTOR****DIGITAL TRANSISTORS  
(BUILT-IN RESISTORS)****■ FEATURES**

- \* Built-in bias resistors that implies easy ON/OFF applications.
- \* The bias resistors are thin-film resistors with complete isolation to allow negative input.

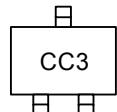
**■ EQUIVALENT CIRCUIT**

\*Pb-free plating product number:DTC123EL

**■ ORDERING INFORMATION**

Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
DTC123E-AE3-6-R	DTC123EL-AE3-6-R	SOT-23	G	I	O	Tape Reel
DTC123E-AL3-6-R	DTC123EL-AL3-6-R	SOT-323	G	I	O	Tape Reel
DTC123E-AN3-6-R	DTC123EL-AN3-6-R	SOT-523	G	I	O	Tape Reel

 (1)Packing Type (2)Pin Assignment (3)Package Type (4)Lead Plating	(1) R: Tape Reel (2) refer to Pin Assignment (3) AE3: SOT-23, AL3: SOT-323, AN3: SOT-523 (4) L: Lead Free Plating, Blank: Pb/Sn
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**■ MARKING**

## ■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

PARAMETER		SYMBOL	RATINGS		UNIT
Supply Voltage		V <sub>CC</sub>	50		V
Input Voltage		V <sub>IN</sub>	-10 ~ +12		V
Output Current		I <sub>OUT</sub>	100		mA
Power Dissipation	SOT-523	P <sub>D</sub>	150		mW
	SOT-23/SOT-323		200		mW
Junction Temperature		T <sub>J</sub>	+150		°C
Storage Temperature		T <sub>STG</sub>	-55 ~ +150		°C

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged.

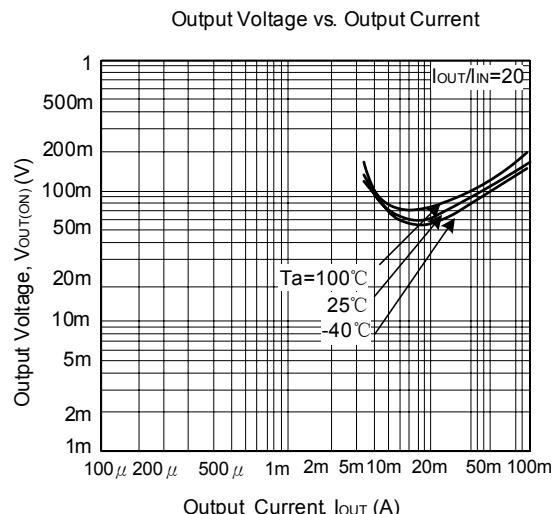
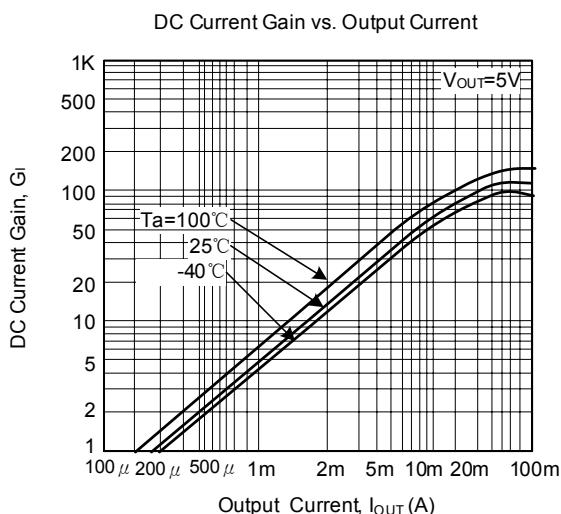
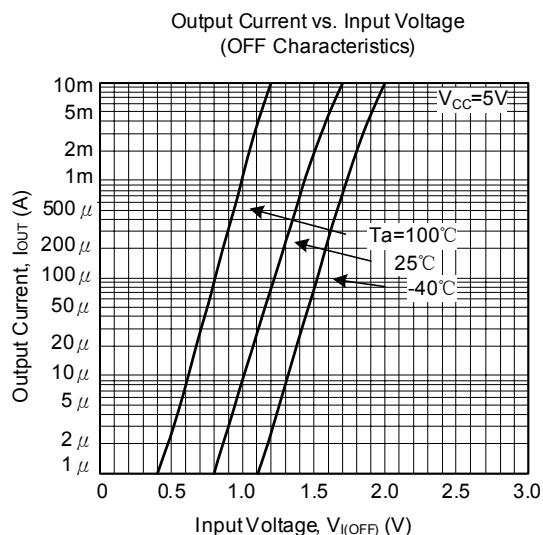
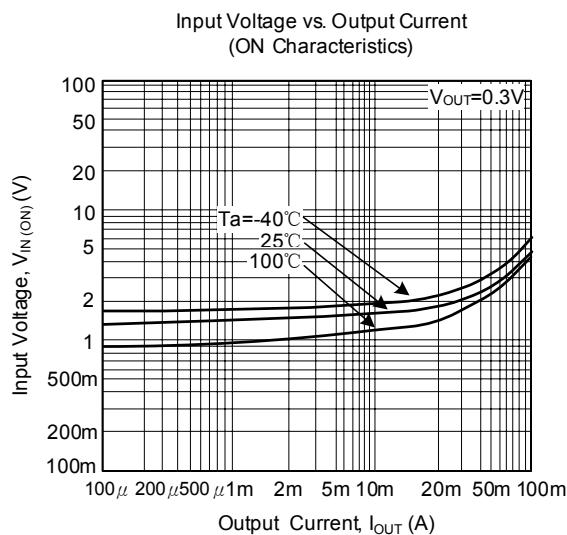
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

## ■ ELECTRICAL SPECIFICATIONS (Ta=25°C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Input Voltage	V <sub>IN(OFF)</sub>	V <sub>CC</sub> =5V, I <sub>OUT</sub> =100µA			0.5	V
	V <sub>IN(ON)</sub>	V <sub>OUT</sub> =0.3V, I <sub>OUT</sub> =20mA	3			
Output Voltage	V <sub>OUT(ON)</sub>	I <sub>OUT</sub> /I <sub>IN</sub> =10mA/0.5mA		0.1	0.3	V
Input Current	I <sub>IN</sub>	V <sub>IN</sub> =5V			3.8	mA
Output Current	I <sub>OUT(OFF)</sub>	V <sub>CC</sub> =50V, V <sub>IN</sub> =0V			0.5	µA
DC Current Gain	G <sub>IN</sub>	V <sub>OUT</sub> =5V, I <sub>OUT</sub> =20mA	20			
Input Resistance	R <sub>1</sub>		1.54	2.2	2.86	KΩ
Resistance Ratio	R <sub>2</sub> /R <sub>1</sub>		0.8	1	1.2	
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>E</sub> =-5mA, f=100MHz *		250		MHz

\* Transition frequency of the device

### ■ TYPICAL CHARACTERISTIC



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.